

1A 40V Low VF(1.00mm)

Chip Information

Chip Size	1.00 x 1.00mm
Pad Size	0.89 x 0.89mm
Chip Quantity	10928 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR		V	
Average Forward Rectified Current	IF(AV)	1000	mA	
Peak Forward Surge Current	IFSM	20	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.385		0.350	V	IF=1000mA Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	2000	800	250	uA	VR=40V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	42	44	55	V	IR=1000uA
Junction Capacitance	Cj			49	pF	VR=10V f=1MHz
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
YJA715	180 +/- 20um	Au(For Eutectic)
YJA717	150 +/- 20um	Au(For Eutectic)
YJA716	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For